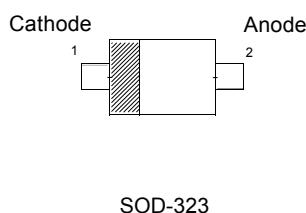
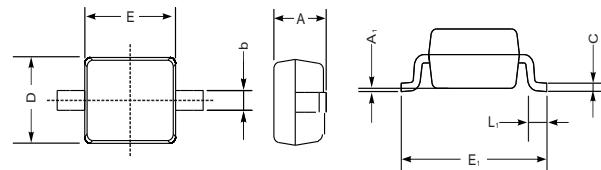


Applications

- High-speed switching



SOD323



UNIT	A	C	D	E	E ₁	b	L ₁	A ₁
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2
mil	max	43	5.9	55	70	108	16	16
	min	32	3.1	47	63	100	9.8	7.9

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Reverse Voltage	V_R	100	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Current $t = 1 \mu\text{s}$ $t = 1 \text{ ms}$ $t = 1 \text{ s}$	I_{FSM}	4 1 0.5	A
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 65 to + 150	°C

BAS316WS

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	V_F	0.715 0.855 1 1.25	V
Reverse Current at $V_R = 25 \text{ V}$ at $V_R = 75 \text{ V}$ at $V_R = 25 \text{ V}, T_J = 150^\circ\text{C}$ at $V_R = 75 \text{ V}, T_J = 150^\circ\text{C}$	I_R	30 1 30 50	nA μA μA μA
Diode Capacitance at $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_{tot}	1.5	pF
Reverse Recovery Time at $I_F = I_R = 10 \text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$	t_{rr}	4	ns

RATING AND CHARACTERISTIC CURVES (BAS316WS)

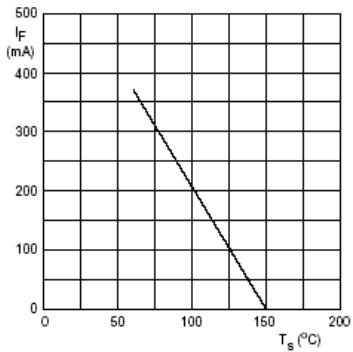


Fig. 1 Maximum permissible continuous forward current as a function of soldering point temperature.

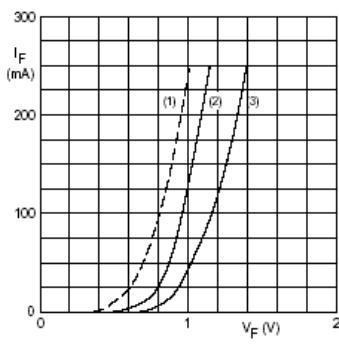
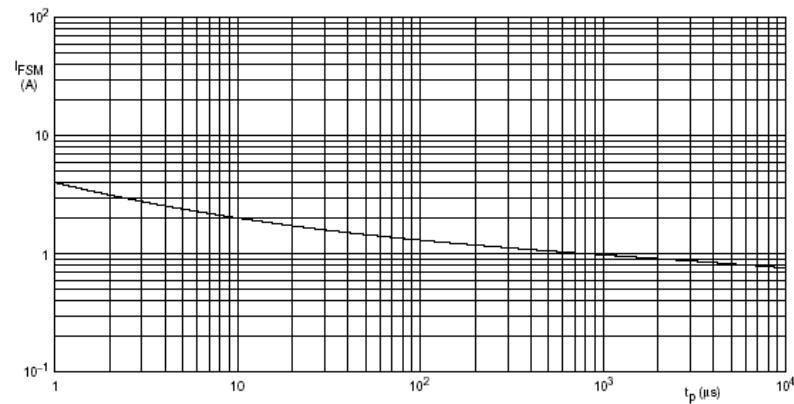


Fig. 2 Forward current as a function of forward voltage.



Based on square wave currents.
T_j = 25 °C prior to surge.

Fig. 3 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

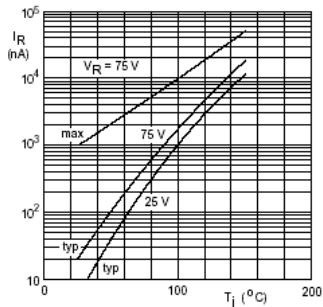


Fig. 4 Reverse current as a function of junction temperature.

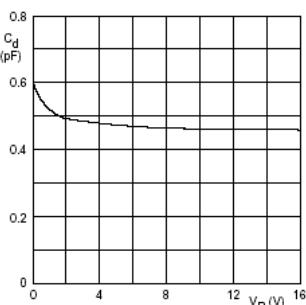


Fig. 5 Diode capacitance as a function of reverse voltage; typical values.